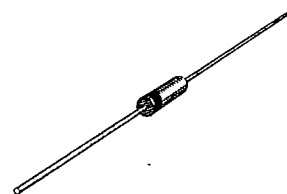


Fast recovery silicon rectifier diodes 1 A, 2 A, 2.5 A, 3 A

T-03-01

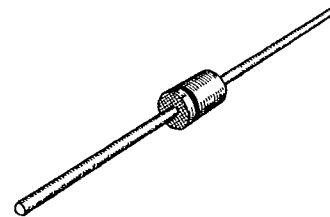
Type	U_{RRM}	U_{RSM}	I_{FAV}	I_{FSM} 8.3 ms	ϑ_{op}	U_F $I_F = 1\text{ A}$ $\vartheta_1 = 25^\circ\text{C}$	I_R at U_{RRM} $\vartheta_1 = 25^\circ\text{C}$	t_{rr} $I_F = +10\text{ mA}$ $I_R = -10\text{ mA}$
	(V)	(V)	(A)	(A)	($^\circ\text{C}$)	(V)	(μA)	(ns)
1N 4933	50	75	1	30	-65 to +175	1.1	5	200*
1N 4934	100	150						
1N 4935	200	250						
1N 4936	400	450						
1N 4937	600	650						
BA 157	400	480	1	35	-65 to +175	1.3	5	300
BA 158	600	720						
BA 159	1 000	1 200						
BYF 401	50	60	1	50	-65 to +175	1.25	10	500
BYF 402	100	120						
BYF 403	200	240						
BYF 404	400	480						
BYF 405	600	720						
BYF 406	800	1 000						
BYF 407	1 000	1 200						



DO-41 mod

* $I_F = 1\text{ A}$, $U_R = 30\text{ A}$

Type	U_{RRM}	U_{RSM}	I_{FAV}	I_{FSM} 8.3 ms	ϑ_{op}	U_F 3 A, 25 $^\circ\text{C}$	I_R at U_{RRM} $\vartheta_1 = 25^\circ\text{C}$	t_{rr} $I_F = +10\text{ mA}$ $I_R = -10\text{ mA}$
	(V)	(V)	(A)	(A)	($^\circ\text{C}$)	(V)	(μA)	(ns)
BY 296	100	120	2	90	-65 to +175	1.3	10	500
BY 297	200	240						
BY 298	400	480						
BY 299	800	1 000						
BYF 500	50	60	2.5	120	-40 to +150	1.25	20	500
BYF 501	100	120						
BYF 502	200	240						
BYF 503	300	360						
BYF 504	400	480						
BYF 505	500	600						
BYF 506	600	720						
BYF 507	800	1 000	3	120	-65 to +175	1.25	10	500
BYF 508	1 000	1 200						
BY 396	100	120						
BY 397	200	240						
BY 398	400	480						
BY 399	800	1 000						



DO-27